For instance, in the fabrication of a photovoltaic solar cell, silicon, which has four valence electrons, is treated to increase its conductivity. On one side of the cell, the impurities, which are phosphorus atoms with five valence electrons (n-donor), donate weakly bound valence electrons to the silicon material, creating excess negative charge carriers. On the other side, atoms of boron with three valence electrons (p-donor) create a greater affinity than silicon to attract electrons. Because the p-type silicon is in intimate contact with the n-type silicon a p-n junction is established and a diffusion of electrons occurs from the region of high electron concentration (the n-type side) into the region of low electron concentration (p-type side). When the electrons diffuse across the p-n junction, they recombine with holes on the p-type side. However, the diffusion of carriers does not occur indefinitely, because the imbalance of charge immediately on either sides of the junction originates an electric field. This electric field forms a diode that promotes current to flow in only one direction. Ohmic metal-semiconductor contacts are made to both the n-type and p-type sides of the solar cell, and the electrodes are ready to be connected to an external load.